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SINGLE DIGIT LED DISPLAY (0.40 Inch)



Lead-Free Parts

LSD401/2SBKS-XX-PF

DATA SHEET

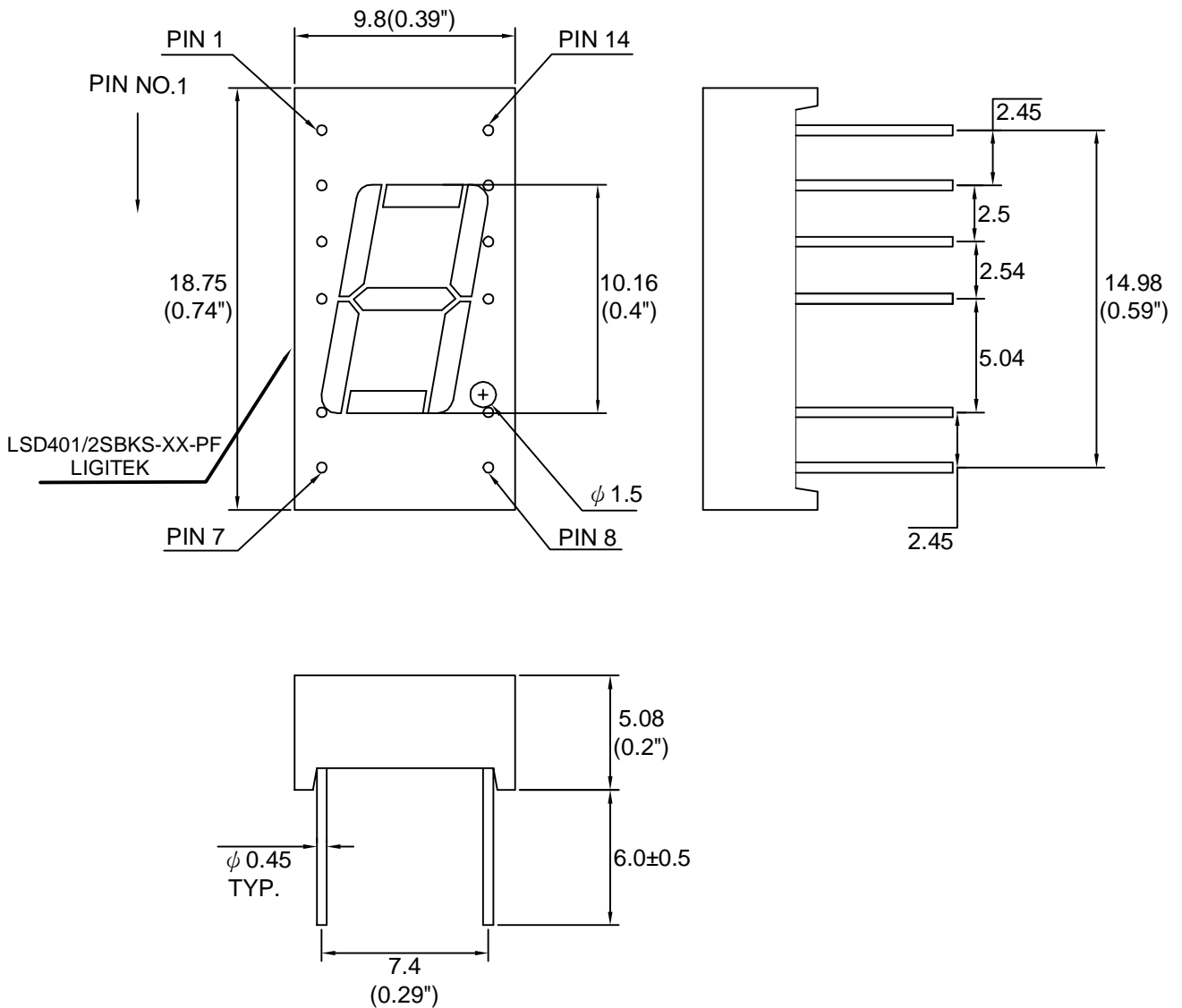
DOC. NO : QW0905- LSD401/2SBKS-XX-PF

REV. : A

DATE : 29 - Sep. - 2008



Package Dimensions



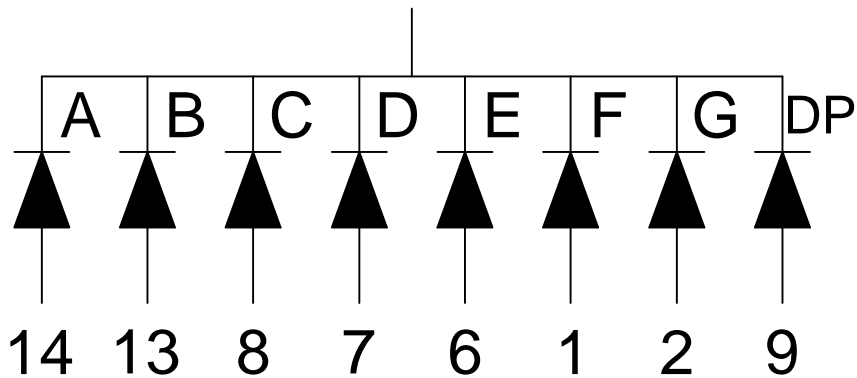
Note : 1.All dimension are in millimeters and (Inch) tolerance is $\pm 0.25(0.01")$ unless otherwise noted.
2.Specifications are subject to change without notice.



Internal Circuit Diagram

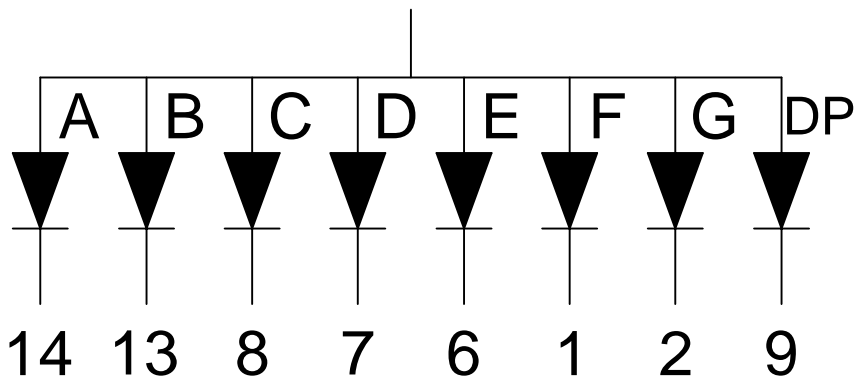
LSD401SBKS-XX-PF

4,12



LSD402SBKS-XX-PF

4,12



NP: 3, 5, 10, 11



Electrical Connection

PIN NO.	LSD401SBKS-XX-PF	PIN NO.	LSD402SBKS-XX-PF
1	Anode F	1	Cathode F
2	Anode G	2	Cathode G
3	No Pin	3	No Pin
4	Common Cathode	4	Common Anode
5	No Pin	5	No Pin
6	Anode E	6	Cathode E
7	Anode D	7	Cathode D
8	Anode C	8	Cathode C
9	Anode DP	9	Cathode DP
10	No Pin	10	No Pin
11	No Pin	11	No Pin
12	Common Cathode	12	Common Anode
13	Anode B	13	Cathode B
14	Anode A	14	Cathode A



Absolute Maximum Ratings at Ta=25 °C

Parameter	Symbol	Ratings	UNIT
		SBKS	
Forward Current Per Chip	IF	30	mA
Peak Forward Current Per Chip (Duty 1/10,0.1ms Pulse Width)	IFP	100	mA
Power Dissipation Per Chip	PD	120	mW
Reverse Current Per Any Chip	Ir	50	μA
Electrostatic Discharge(*)	ESD	500	V
Operating Temperature	Topr	-20 ~ +80	°C
Storage Temperature	Tstg	-30 ~ +100	°C

* Static Electricity or power surge will damage the LED. Use of a conductive wrist band or anti-electrostatic glove is recommended when handling these LED. All devices, equipment and machinery must be properly grounded.

Part Selection And Application Information(Ratings at 25°C)

PART NO	CHIP		common cathode or anode	λ D (nm)	Δ λ (nm)	Electrical				IV-M
	Material	Emitted				Vf(v)		Iv(mcd)		
						Typ.	Max.	Min.	Typ.	
LSD401SBKS-XX-PF	InGaN/SiC	Blue	Common Cathode	460	26	3.5	4.2	8.5	12.8	2:1
LSD402SBKS-XX-PF			Common Anode							

Note : 1.The forward voltage data did not including ±0.1V testing tolerance.
2. The luminous intensity data did not including ±15% testing tolerance.

**Test Condition For Each Parameter**

Parameter	Symbol	Unit	Test Condition
Forward Voltage Per Chip	V _f	volt	I _f =20mA
Luminous Intensity Per Chip	I _v	mcd	I _f =10mA
Dominant Wavelength	λ_D	nm	I _f =20mA
Spectral Line Half-Width	$\Delta \lambda$	nm	I _f =20mA
Reverse Current Any Chip	I _r	μA	V _r =5V
Luminous Intensity Matching Ratio	IV-M		



Typical Electro-Optical Characteristics Curve

SBK-S CHIP

Fig.1 Forward current vs. Forward Voltage

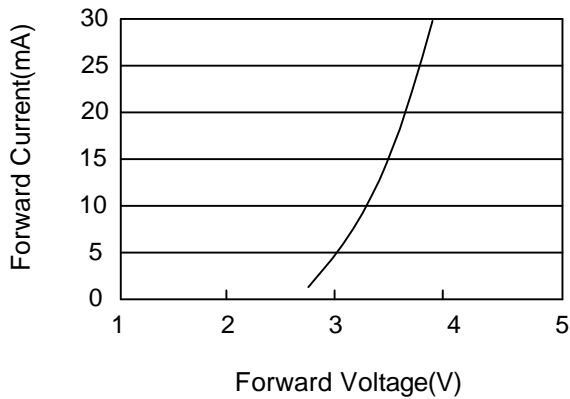


Fig.2 Relative Intensity vs. Forward Current

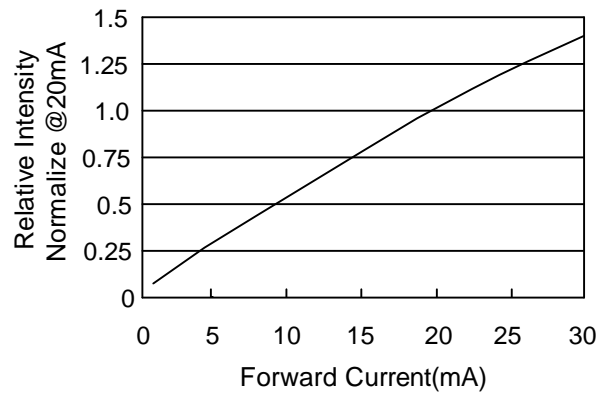


Fig.3 Forward Current vs. Temperature

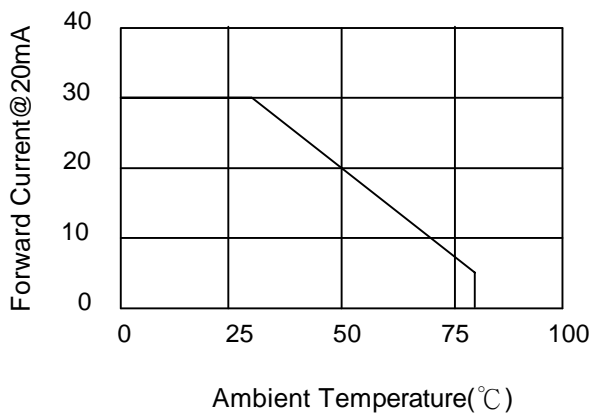
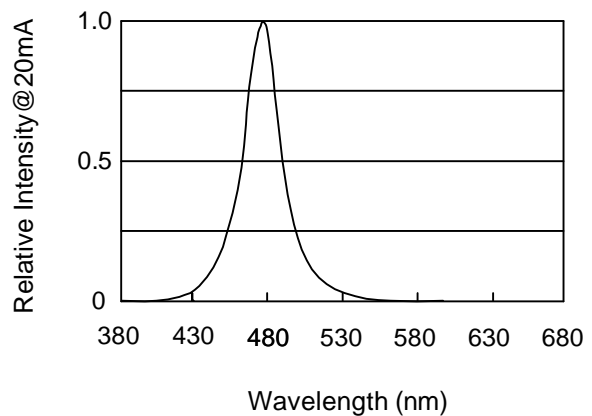


Fig.4 Relative Intensity vs. Wavelength





Soldering Condition(Pb-Free)

1.Iron:

Soldering Iron:30W Max

Temperature 350 ° C Max

Soldering Time:3 Seconds Max(One time only)

Distance:Solder Temperature 1/16 Inch Below Seating
Plane For 3 Seconds At 260 ° C

2.Wave Soldering Profile

Dip Soldering

Preheat: 120° C Max

Preheat time: 60seconds Max

Ramp-up

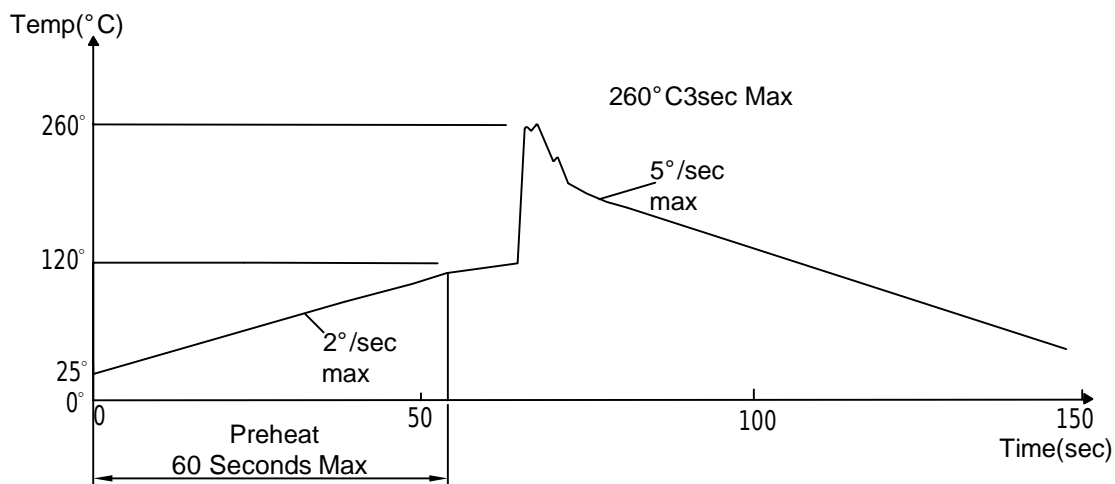
2° C/sec(max)

Ramp-Down:-5° C/sec(max)

Solder Bath:260° C Max

Dipping Time:3 seconds Max

Distance:Solder Temperature 1/16 Inch Below Seating
Plane For 3 Seconds At 260° C



Note: 1.Wave solder should not be made more than one time.
2.You can just only select one of the soldering conditions as above.

**Reliability Test:**

Test Item	Test Condition	Description	Reference Standard
Operating Life Test	1.Under Room Temperature 2.If=10mA 3.t=1000 hrs (-24hrs, +72hrs)	This test is conducted for the purpose of determining the resistance of a part in electrical and thermal stressed.	MIL-STD-750: 1026 MIL-STD-883: 1005 JIS C 7021: B-1
High Temperature Storage Test	1.Ta=105 °C±5°C 2.t=1000 hrs (-24hrs, +72hrs)	The purpose of this is the resistance of the device which is laid under condition of high temperature for hours.	MIL-STD-883:1008 JIS C 7021: B-10
Low Temperature Storage Test	1.Ta=-40 °C±5°C 2.t=1000 hrs (-24hrs, +72hrs)	The purpose of this is the resistance of the device which is laid under condition of low temperature for hours.	JIS C 7021: B-12
High Temperature High Humidity Test	1.Ta=65 °C±5°C 2.RH=90%~95% 3.t=240hrs ±2hrs	The purpose of this test is the resistance of the device under tropical for hours.	MIL-STD-202:103B JIS C 7021: B-11
Thermal Shock Test	1.Ta=105 °C±5°C & -40 °C±5°C (10min) (10min) 2.total 10 cycles	The purpose of this is the resistance of the device to sudden extreme changes in high and low temperature.	MIL-STD-202: 107D MIL-STD-750: 1051 MIL-STD-883: 1011
Solder Resistance Test	1.T.Sol=260 °C±5°C 2.Dwell time= 10 ±1sec.	This test intended to determine the thermal characteristic resistance of the device to sudden exposures at extreme changes in temperature when soldering the lead wire.	MIL-STD-202: 210A MIL-STD-750: 2031 JIS C 7021: A-1
Solderability Test	1.T.Sol=230 °C±5°C 2.Dwell time=5 ±1sec	This test intended to see soldering well performed or not.	MIL-STD-202: 208D MIL-STD-750: 2026 MIL-STD-883: 2003 JIS C 7021: A-2